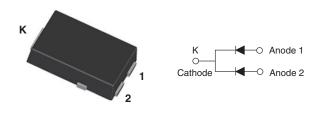
Vishay Semiconductors





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SMPC (TO-277A)

| PRIMARY CHARACTERISTICS | | | | | |
|----------------------------------|----------------|--|--|--|--|
| I _{F(AV)} | 2 x 3 A | | | | |
| V _R | 100 V | | | | |
| V _F at I _F | 0.75 V | | | | |
| t _{rr (typ.)} | 27 ns | | | | |
| T _J max. | 175 °C | | | | |
| Package | SMPC (TO-277A) | | | | |
| Circuit configuration | Dual serial | | | | |

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

| ABSOLUTE MAXIMUM RATINGS | | | | | | | |
|---|------------|-----------------------------------|---|-------------|-------|--|--|
| PARAMETER | | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | |
| Peak repetitive reverse voltage | | V _{RRM} | | 100 | V | | |
| Average restified forward surrent | per device | I _{F(AV)} | T _{Sp} = 165 °C | 6 | | | |
| Average rectified forward current | per diode | | | 3 | A | | |
| Non repetitive peak ourse oursent | per device | I _{FSM} | T _J = 25 °C, 6 ms square pulse | 150 | | | |
| Non-repetitive peak surge current | per diode | | | 80 | | | |
| Operating junction and storage temperatures | | T _J , T _{Stg} | | -65 to +175 | °C | | |

| ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified) | | | | | | | |
|--|-------------------------------------|---|------|------|------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | I _R = 100 μA | 100 | - | - | v | |
| Forward valtage, per diade | V _F | I _F = 3 A | - | 0.87 | 0.94 | | |
| Forward voltage, per diode | | I _F = 3 A, T _J = 125 °C | - | 0.75 | 0.79 | | |
| Deverse lectrose current, per diada | I _R | V _R = V _R rated | - | - | 2 | μA | |
| Reverse leakage current, per diode | | $T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$ | - | 0.7 | 10 | | |
| Junction capacitance | CT | V _R = 100 V | - | 13 | - | pF | |

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RoHS

COMPLIANT

HALOGEN

FREE



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| DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified) | | | | | | | | | |
|---|------------------|---|--|------|------|------|-------|--|--|
| PARAMETER | SYMBOL | TEST CO | NDITIONS | MIN. | TYP. | MAX. | UNITS | | |
| | t _{rr} | $I_F=1~A,~dI_F/dt=50~A/\mu s,~V_R=30~V$ | | - | 27 | - | | | |
| Povereo recover timo | | $I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$ | | - | - | 25 | | | |
| Reverse recovery time | | T _J = 25 °C | | - | 20 | - | A nC | | |
| | | T _J = 125 °C | I _F = 3 A dI _F /dt = 200 A/μs V _R = 160 V | - | 26 | - | | | |
| Deals receiver sourcent | I _{RRM} | T _J = 25 °C | | - | 2.4 | - | | | |
| Peak recovery current | | T _J = 125 °C | | - | 3.8 | - | | | |
| | Q _{rr} | T _J = 25 °C | | - | 23 | - | | | |
| Reverse recovery charge | | T _J = 125 °C | | - | 50 | - | | | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | |
|---|-----------------------------------|---------------------------|------|--------|------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -65 | - | 175 | °C | |
| Thermal resistance, junction to solder pad, per diode | R _{thJ-Sp} | | - | 2.8 | 4 | °C/W | |
| Approvimeto weight | | | | 0.1 | | g | |
| Approximate weight | | | | 0.0035 | | oz. | |
| Marking device | | Case style SMPC (TO-277A) | | NC | H1 | | |

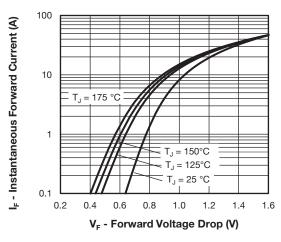


Fig. 1 - Typical Forward Voltage Drop Characteristics

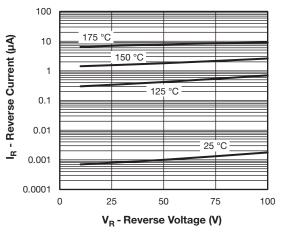
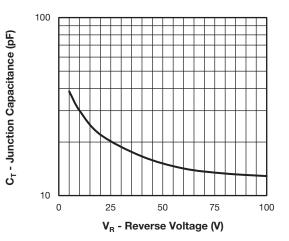


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

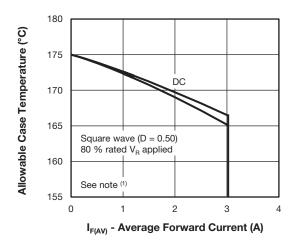
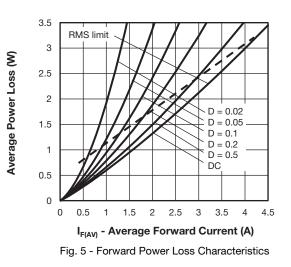


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current



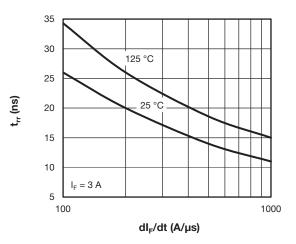


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

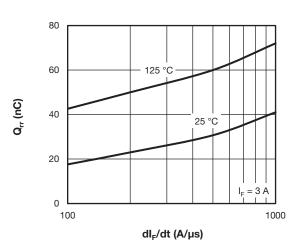


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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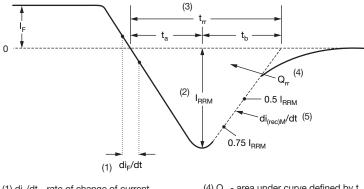
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VS-6CSH01HM3

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- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) ${\rm Q}_{\rm rr}$ - area under curve defined by ${\rm t}_{\rm rr}$ and ${\rm I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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Device code

| le | vs- | • | 6 | с | S | н | 01 | н | М3 | | | | | | | |
|----|-----------------------------------|-------------------------|------|---------------------------|-----------|--------|---------|---------|---------|--|--|--|--|--|--|--|
| I | 1 | | 2 | 3 | 4 | 5 | 6 | (7) | 8 | | | | | | | |
| | 1 - Vishay Semiconductors product | | | | | | | | | | | | | | | |
| | 2 | - | Cur | rent rati | ng (6 =) | 6 A) | | | | | | | | | | |
| | 3 | - | Circ | cuit conf | iguratior | า: | | | | | | | | | | |
| | | | C = | C = common cathode | | | | | | | | | | | | |
| | 4 | - | S = | S = SMPC package | | | | | | | | | | | | |
| | 5 | - | Pro | Process type, | | | | | | | | | | | | |
| | | H = hyper fast recovery | | | | | | | | | | | | | | |
| | 6 | - | Volt | Voltage code (01 = 100 V) | | | | | | | | | | | | |
| | 7 | - | H = | H = AEC-Q101 qualified | | | | | | | | | | | | |
| | 8 | - | M3 | = halog | en-free, | RoHS-0 | complia | nt, and | termina | M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free | | | | | | |

| ORDERING INFORMATION (Example) | | | | | | | |
|--------------------------------|-------------------|------------------------|------------------------------------|--|--|--|--|
| PREFERRED P/N | QUANTITY PER REEL | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION | | | | |
| VS-6CSH01HM3/86A | 1500 | 1500 | 7" diameter plastic tape and reel | | | | |
| VS-6CSH01HM3/87A | 6500 | 6500 | 13" diameter plastic tape and reel | | | | |

| LINKS TO RELATED DOCUMENTS | | | | | |
|----------------------------|--------------------------|--|--|--|--|
| Dimensions | www.vishay.com/doc?95570 | | | | |
| Part marking information | www.vishay.com/doc?95565 | | | | |
| Packaging information | www.vishay.com/doc?88869 | | | | |
| SPICE model | www.vishay.com/doc?96378 | | | | |

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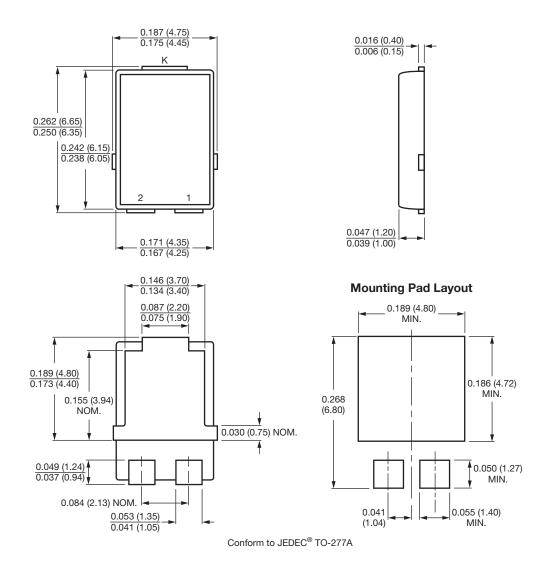
Outline Dimensions





TO-277A (SMPC)

DIMENSIONS in inches (millimeters)





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